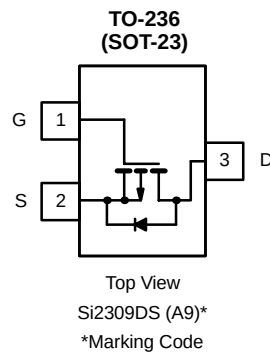




P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-60	0.340 @ $V_{GS} = -10$ V	-1.25
	0.550 @ $V_{GS} = -4.5$ V	-1



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^{a, b}	$T_A = 25^\circ\text{C}$	I_D	-1.25	A
	$T_A = 100^\circ\text{C}$		-0.85	
Pulsed Drain Current		I_{DM}	-8	
Avalanche Current		I_{AS}	-5	
Maximum Power Dissipation ^{a, b}	$T_A = 25^\circ\text{C}$	P_D	1.25	W
	$T_A = 70^\circ\text{C}$		0.8	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{thJA}		100	$^\circ\text{C/W}$
	Steady State		130	166	
Maximum Junction-to-Lead ^a	Steady State	R_{thJL}	45	60	

Notes

- a. Surface Mounted on FR4 Board.
b. $t \leq 5$ sec.

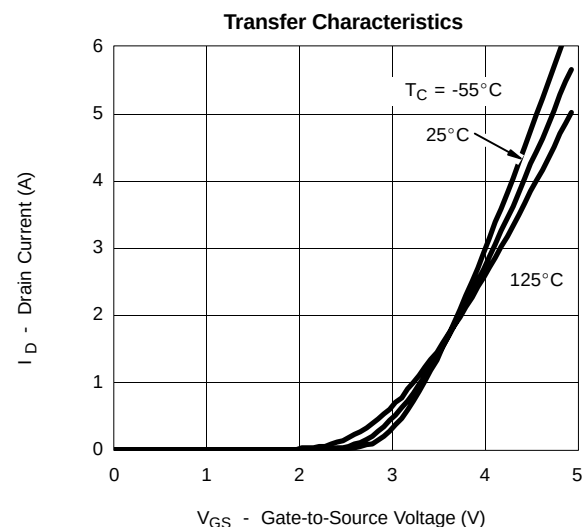
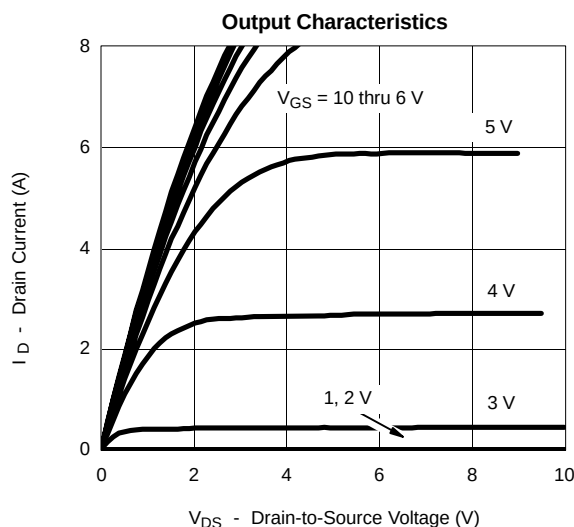
SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{DS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1			
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -48\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -48\text{ V}, V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$			-50	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq -4.5\text{ V}, V_{GS} = -10\text{ V}$	-6			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -1.25\text{ A}$		0.275	0.340	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -1\text{ A}$		0.406	0.550	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -4.5\text{ V}, I_D = -1\text{ A}$		1.9		S
Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = -30\text{ V}, V_{GS} = -10\text{ V}, I_D = -1.25\text{ A}$		5.4	12	nC
Gate-Source Charge	Q_{gs}			1.15		
Gate-Drain Charge	Q_{gd}			0.92		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -30\text{ V}, R_L = 30\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\text{ }\Omega$		10.5	20	ns
Rise Time	t_r			11.5	20	
Turn-Off Delay Time	$t_{d(off)}$			15.5	30	
Fall Time	t_f			7.5	15	
Source-Drain Rating Characteristics ^b						
Continuous Current	I_S				-1.25	A
Pulsed Current	I_{SM}				-8	
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.25\text{ A}, V_{GS} = 0\text{ V}$		-0.82	-1.2	V
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.25\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		30	55	ns

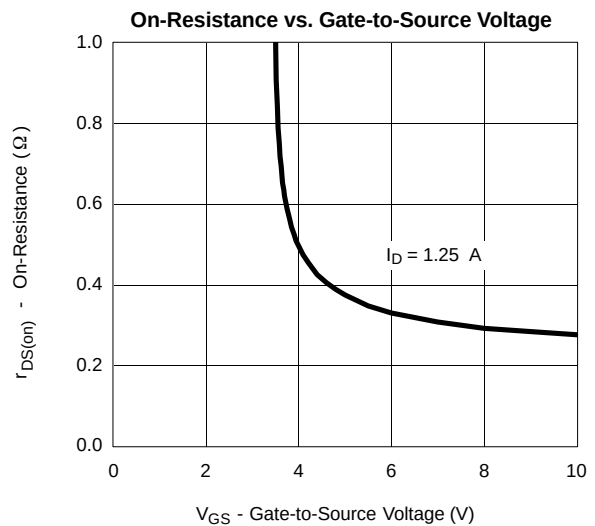
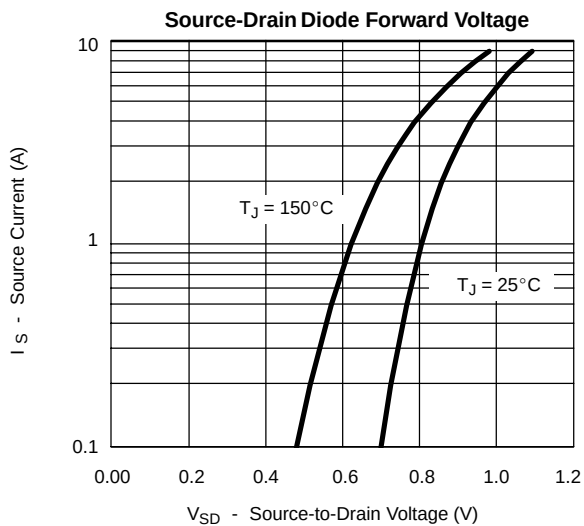
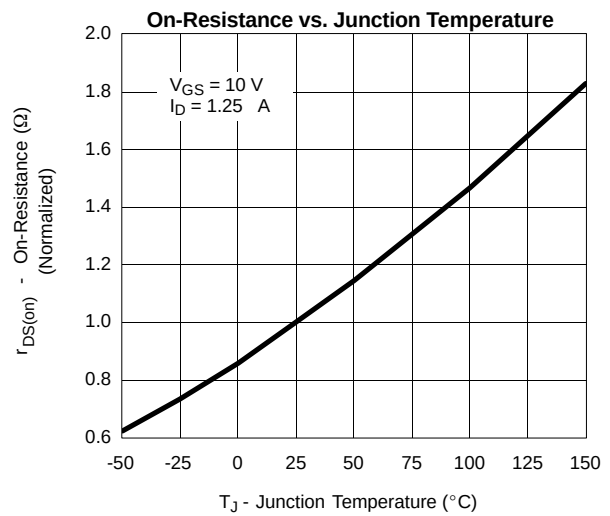
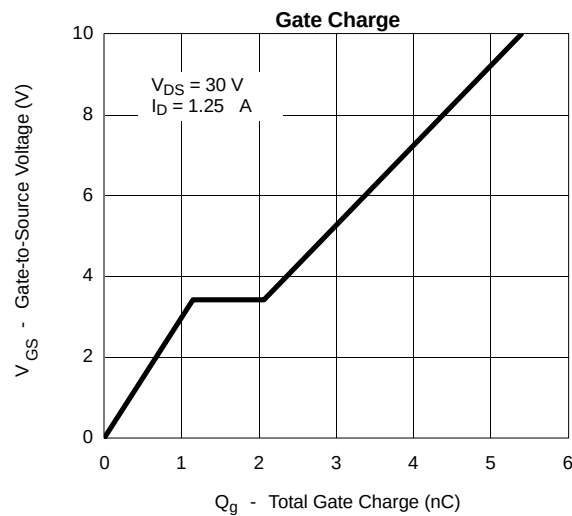
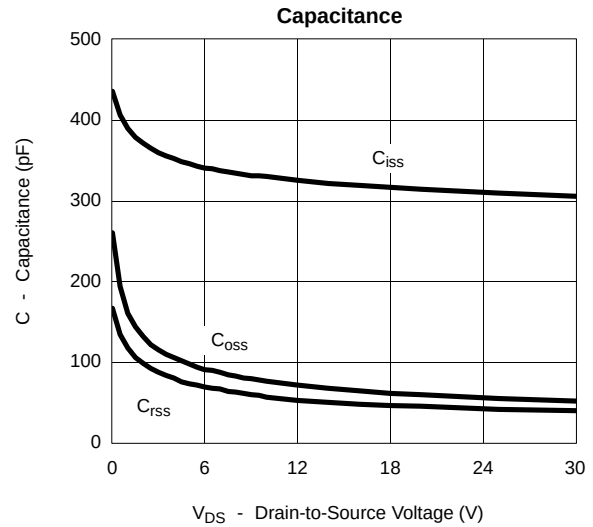
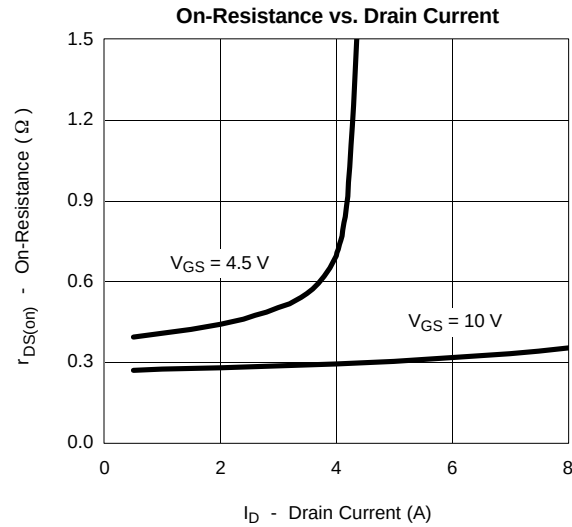
Notes

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

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